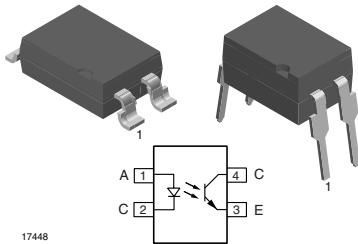


Optocoupler, Phototransistor Output, High Reliability, 5300 V_{RMS}



17448

DESCRIPTION

The SFH615A (DIP) and SFH6156 (SMD) feature a variety of transfer ratios, low coupling capacitance and high isolation voltage. These couplers have a GaAs infrared diode emitter, which is optically coupled to a silicon planar phototransistor detector, and is incorporated in a plastic DIP-4 or SMD package.

The coupling devices are designed for signal transmission between two electrically separated circuits.

The couplers are end-stackable with 2.54 mm lead spacing. Creepage and clearance distances of > 8.0 mm are achieved with option 6. This version complies with IEC 60950 (DIN VDE 0805) for reinforced insulation up to an operation voltage of 400 V_{RMS} or DC. Specifications subject to change.

FEATURES

- Excellent CTR linearity depending on forward current
- Isolation test voltage, 5300 V_{RMS}
- Fast switching times
- Low CTR degradation
- Low coupling capacitance
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC


RoHS
COMPLIANT

APPLICATIONS

- Switchmode power supply
- Telecom
- Battery powered equipment

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- DIN EN 60747-5-5 (VDE 0884) available with option 1

ORDER INFORMATION

PART	REMARKS
SFH615A-1	CTR 40 % to 80 %, DIP-4
SFH615A-2	CTR 63 % to 125 %, DIP-4
SFH615A-3	CTR 100 % to 200 %, DIP-4
SFH615A-4	CTR 160 % to 320 %, DIP-4
SFH6156-1	CTR 40 % to 80 %, SMD-4
SFH6156-2	CTR 63 % to 125 %, SMD-4
SFH6156-3	CTR 100 % to 200 %, SMD-4
SFH6156-4	CTR 160 % to 320 %, SMD-4
SFH615A-1X006	CTR 40 % to 80 %, DIP-4 400 mil (option 6)
SFH615A-1X007	CTR 40 % to 80 %, SMD-4 (option 7)
SFH615A-2X006	CTR 63 % to 125 %, DIP-4 400 mil (option 6)
SFH615A-2X007	CTR 63 % to 125 %, SMD-4 (option 7)
SFH615A-2X009	CTR 63 % to 125 %, SMD-4 (option 9)
SFH615A-3X006	CTR 100 % to 200 %, DIP-4 400 mil (option 6)
SFH615A-3X007	CTR 100 % to 200 %, SMD-4 (option 7)
SFH615A-3X008	CTR 100 % to 200 %, SMD-4 (option 8)
SFH615A-3X009	CTR 100 % to 200 %, SMD-4 (option 9)
SFH615A-4X006	CTR 160 % to 320 %, DIP-4 400 mil (option 6)
SFH615A-4X007	CTR 160 % to 320 %, SMD-4 (option 7)
SFH615A-4X008	CTR 160 % to 320 %, SMD-4 (option 8)
SFH615A-4X009	CTR 160 % to 320 %, SMD-4 (option 9)

Note

For additional information on the available options refer to option information. See tape and reel section for 4 pin optocouplers T0 with 90° rotation.

ABSOLUTE MAXIMUM RATINGS (1)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V _R	6	V
DC forward current		I _F	60	mA
Surge forward current	t _p ≤ 10 μs	I _{FSM}	2.5	A
OUTPUT				
Collector emitter voltage		V _{CE}	70	V
Emitter collector voltage		V _{ECO}	7	V
Collector current		I _C	50	mA
	t _p ≤ 1.0 ms	I _C	100	mA
COUPLER				
Isolation test voltage between emitter and detector	t = 1.0 s	V _{ISO}	5300	V _{RMS}
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Insulation thickness between emitter and detector			≥ 0.4	mm
Comparative tracking index per DIN IEC112/VDE 0303 part 1		CTI	≥ 175	
Isolation resistance	V _{IO} = 500 V, T _{amb} = 25 °C	R _{IO}	≥ 10 ¹²	Ω
	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	≥ 10 ¹¹	Ω
Storage temperature range		T _{stg}	- 55 to + 150	°C
Ambient temperature range		T _{amb}	- 55 to +100	°C
Soldering temperature (2)	max. 10 s, dip soldering distance to seating plane ≥ 1.5 mm	T _{slid}	260	°C

Notes

(1) T_{amb} = 25 °C, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

(2) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

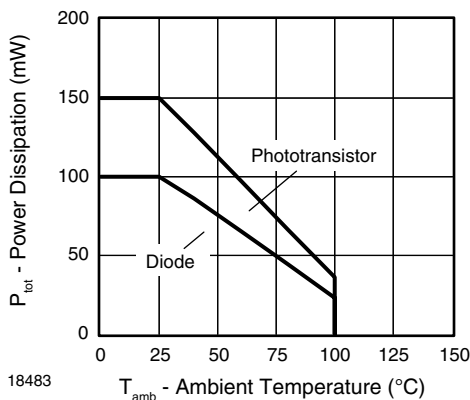


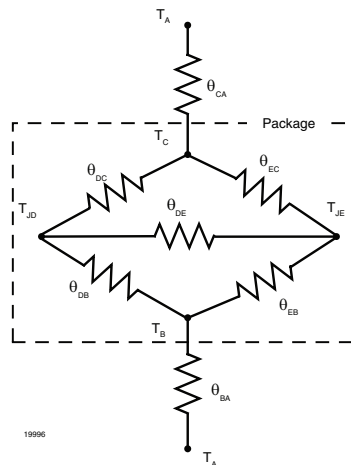
Fig. 1 - Permissible Power Dissipation vs. Ambient Temperature



THERMAL CHARACTERISTICS (1)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
LED power dissipation	at 25 °C	P _{diss}	100	mW
Output power dissipation	at 25 °C	P _{diss}	150	mW
Maximum LED junction temperature		T _{jmax}	125	°C
Maximum output die junction temperature		T _{jmax}	125	°C
Thermal resistance, junction emitter to board		θ _{EB}	173	°C/W
Thermal resistance, junction emitter to case		θ _{EC}	149	°C/W
Thermal resistance, junction detector to board		θ _{DB}	111	°C/W
Thermal resistance, junction detector to case		θ _{DC}	127	°C/W
Thermal resistance, junction emitter to junction detector		θ _{ED}	95	°C/W
Thermal resistance, board to ambient (2)		θ _{BA}	195	°C/W
Thermal resistance, case to ambient (2)		θ _{CA}	3573	°C/W

Notes

- (1) The thermal model is represented in the thermal network below. Each resistance value given in this model can be used to calculate the temperatures at each node for a given operating condition. The thermal resistance from board to ambient will be dependent on the type of PCB, layout and thickness of copper traces. For a detailed explanation of the thermal model, please reference Vishay's thermal characteristics of optocouplers application note.
- (2) For 2 layer FR4 board (4" x 3" x 0.062)



ELECTRICAL CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	I _F = 60 mA		V _F		1.25	1.65	V
Reverse current	V _R = 6 V		I _R		0.01	10	μA
Capacitance	V _R = 0 V, f = 1 MHz		C _O		13		pF
OUTPUT							
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz		C _{CE}		5.2		pF
Collector emitter leakage current	V _{CE} = 10 V	SFH615A-1	I _{CEO}		2	50	nA
		SFH6156-1	I _{CEO}		2	50	nA
		SFH615A-2	I _{CEO}		2	50	nA
		SFH6156-2	I _{CEO}		2	50	nA
		SFH615A-3	I _{CEO}		5	100	nA
		SFH6156-3	I _{CEO}		5	100	nA
		SFH615A-4	I _{CEO}		5	100	nA
SFH6156-4	I _{CEO}		5	100	nA		

ELECTRICAL CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
COUPLER							
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 2.5 \text{ mA}$		V_{CEsat}		0.25	0.4	V
Coupling capacitance			C_C		0.4		pF

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	SFH615A-1	CTR	40		80	%
		SFH6156-1	CTR	40		80	%
		SFH615A-2	CTR	63		125	%
		SFH6156-2	CTR	63		125	%
		SFH615A-3	CTR	100		200	%
		SFH6156-3	CTR	100		200	%
		SFH615A-4	CTR	160		320	%
		SFH6156-4	CTR	160		320	%
	$I_F = 1 \text{ mA}, V_{CE} = 5 \text{ V}$	SFH615A-1	CTR	13	30		%
		SFH6156-1	CTR	13	30		%
		SFH615A-2	CTR	22	45		%
		SFH6156-2	CTR	22	45		%
		SFH615A-3	CTR	34	70		%
		SFH6156-3	CTR	34	70		%
SFH615A-4	CTR	56	90		%		
SFH6156-4	CTR	56	90		%		

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
NON-SATURATED							
Rise time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, T_A = 25 \text{ }^\circ\text{C}, R_L = 75 \text{ } \Omega$		t_r		2		μs
Fall time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, T_A = 25 \text{ }^\circ\text{C}, R_L = 75 \text{ } \Omega$		t_f		2		μs
Turn-on time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, T_A = 25 \text{ }^\circ\text{C}, R_L = 75 \text{ } \Omega$		t_{on}		3		μs
Turn-off time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, T_A = 25 \text{ }^\circ\text{C}, R_L = 75 \text{ } \Omega$		t_{off}		2.3		μs
Cut-off frequency	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, T_A = 25 \text{ }^\circ\text{C}, R_L = 75 \text{ } \Omega$		f_{ctr}		250		kHz
SATURATED							
Rise time	$V_{CC} = 5 \text{ V}, T_A = 25 \text{ }^\circ\text{C}, R_L = 1 \text{ k}\Omega, I_F = 20 \text{ mA}$	SFH615A-1	t_r		2		μs
		SFH6156-1					
	$V_{CC} = 5 \text{ V}, T_A = 25 \text{ }^\circ\text{C}, R_L = 1 \text{ k}\Omega, I_F = 10 \text{ mA}$	SFH615A-2	t_r		3		μs
		SFH6156-2					
		SFH615A-3					
		SFH6156-3					
$V_{CC} = 5 \text{ V}, T_A = 25 \text{ }^\circ\text{C}, R_L = 1 \text{ k}\Omega, I_F = 5.0 \text{ mA}$	SFH615A-4	t_r		4		μs	
	SFH6156-4						



SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
SATURATED							
Fall time	$V_{CC} = 5\text{ V}, T_A = 25\text{ }^\circ\text{C}, R_L = 1\text{ k}\Omega, I_F = 20\text{ mA}$	SFH615A-1	t_f		11		μs
		SFH6156-1					
	$V_{CC} = 5\text{ V}, T_A = 25\text{ }^\circ\text{C}, R_L = 1\text{ k}\Omega, I_F = 10\text{ mA}$	SFH615A-2	t_f		14		μs
		SFH6156-2					
		SFH615A-3					
		SFH6156-3					
$V_{CC} = 5\text{ V}, T_A = 25\text{ }^\circ\text{C}, R_L = 1\text{ k}\Omega, I_F = 5\text{ mA}$	SFH615A-4	t_f		15		μs	
	SFH6156-4						
Turn-on time	$V_{CC} = 5\text{ V}, T_A = 25\text{ }^\circ\text{C}, R_L = 1\text{ k}\Omega, I_F = 20\text{ mA}$	SFH615A-1	t_{on}		3		μs
		SFH6156-1					
	$V_{CC} = 5\text{ V}, T_A = 25\text{ }^\circ\text{C}, R_L = 1\text{ k}\Omega, I_F = 10\text{ mA}$	SFH615A-2	t_{on}		4.2		μs
		SFH6156-2					
		SFH615A-3					
		SFH6156-3					
$V_{CC} = 5\text{ V}, T_A = 25\text{ }^\circ\text{C}, R_L = 1\text{ k}\Omega, I_F = 5\text{ mA}$	SFH615A-4	t_{on}		6		μs	
	SFH6156-4						
Turn-off time	$V_{CC} = 5\text{ V}, T_A = 25\text{ }^\circ\text{C}, R_L = 1\text{ k}\Omega, I_F = 20\text{ mA}$	SFH615A-1	t_{off}		18		μs
		SFH6156-1					
	$V_{CC} = 5\text{ V}, T_A = 25\text{ }^\circ\text{C}, R_L = 1\text{ k}\Omega, I_F = 10\text{ mA}$	SFH615A-2	t_{off}		23		μs
		SFH6156-2					
		SFH615A-3					
		SFH6156-3					
$V_{CC} = 5\text{ V}, T_A = 25\text{ }^\circ\text{C}, R_L = 1\text{ k}\Omega, I_F = 5\text{ mA}$	SFH615A-4	t_{off}		25		μs	
	SFH6156-4						

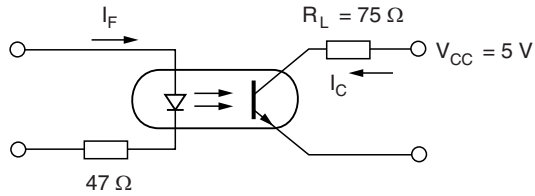
SAFETY AND INSULATION RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Climatic classification (according to IEC 68 part 1)				55/100/21		
Comparative tracking index		CTI	175		399	
V_{IOTM}			10000			V
V_{IORM}			890			V
P_{SO}					400	mW
I_{SI}					275	mA
T_{SI}					175	$^\circ\text{C}$
Creepage distance	standard DIP-4		7			mm
Clearance distance	standard DIP-4		7			mm
Creepage distance	400 mil DIP-4		8			mm
Clearance distance	400 mil DIP-4		8			mm
Insulation thickness, reinforced rated	per IEC 60950 2.10.5.1		0.4			mm

Note

As per IEC 60747-5-2, § 7.4.3.8.1, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

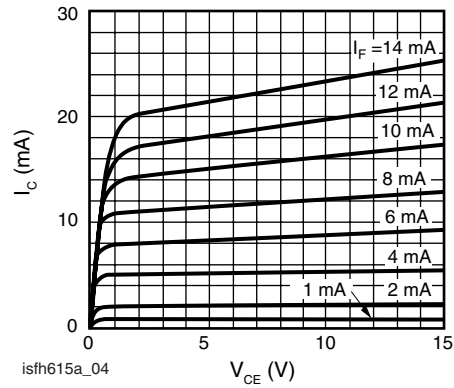
TYPICAL CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified



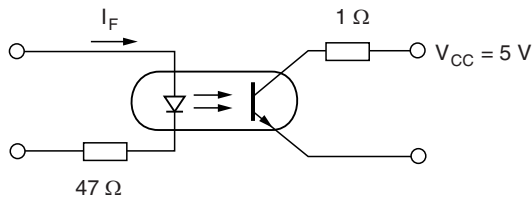
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Fig. 2 - Linear Operation (without Saturation)



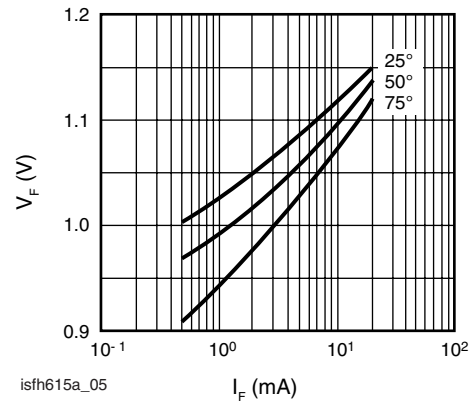
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Fig. 5 - Output Characteristics (Typ.) Collector Current vs. Collector Emitter Voltage



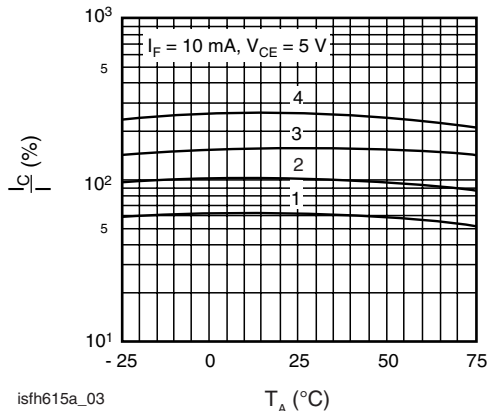
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Fig. 3 - Switching Operation (with Saturation)



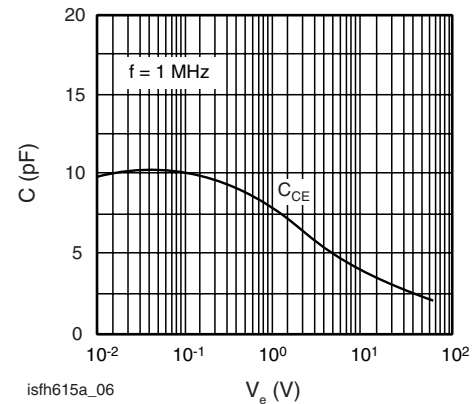
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Fig. 6 - Diode Forward Voltage (Typ.) vs. Forward Current



isfh615a_03

Fig. 4 - Current Transfer Ratio (Typ.) vs. Temperature



isfh615a_06

Fig. 7 - Transistor Capacitance (Typ.) vs. Collector Emitter Voltage

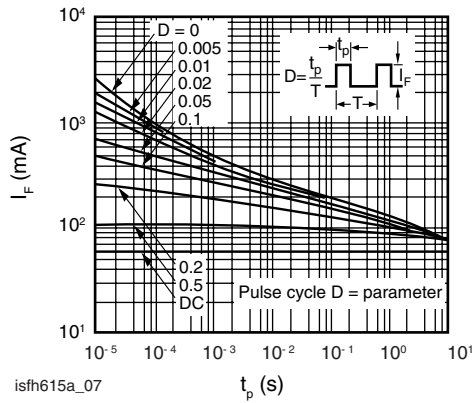
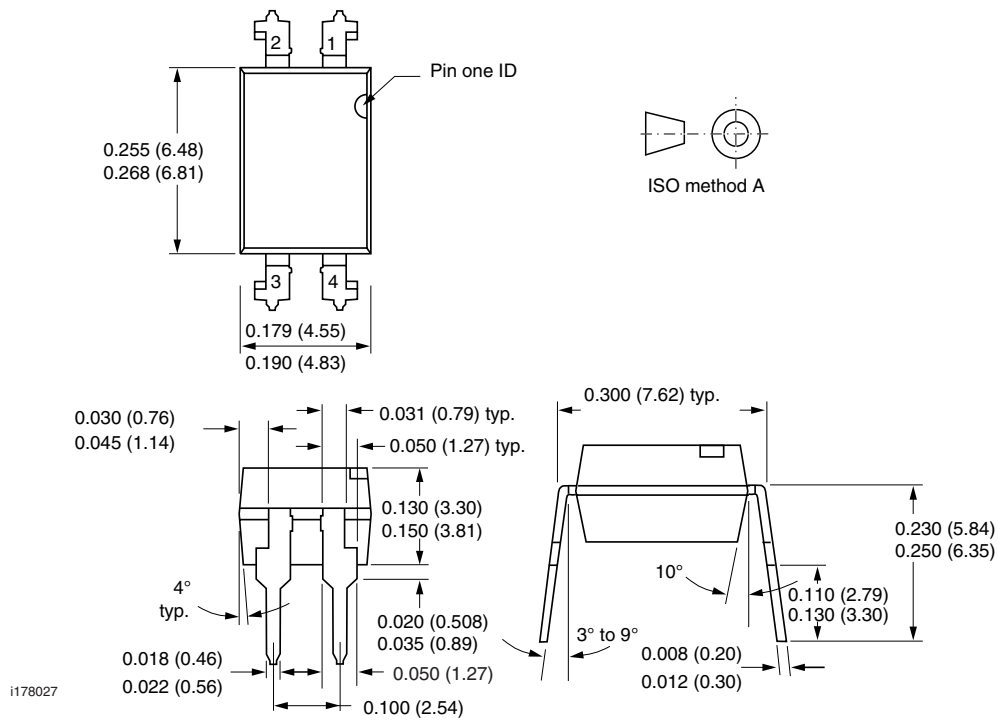


Fig. 8 - Permissible Pulse Handling Capability Forward Current vs. Pulse Width

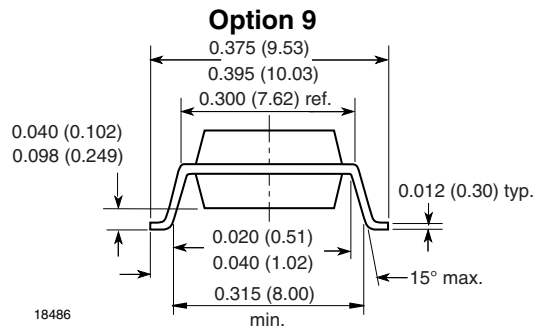
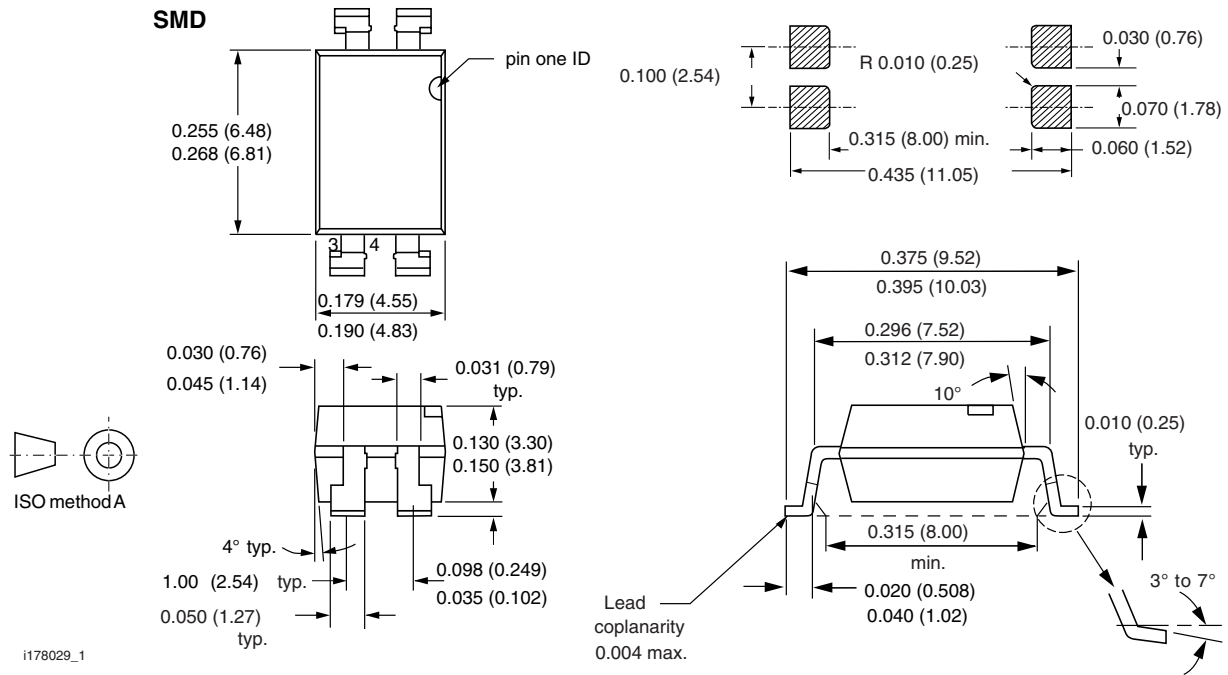
PACKAGE DIMENSIONS in inches (millimeters)



SFH615A, SFH6156

Vishay Semiconductors

Optocoupler, Phototransistor Output,
High Reliability, 5300 V_{RMS}



**OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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